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Mechanisms in Materials**

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Positron annihilation in oxides

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**Forschungszentrum
Dresden Rossendorf**

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Outline

- ZnO

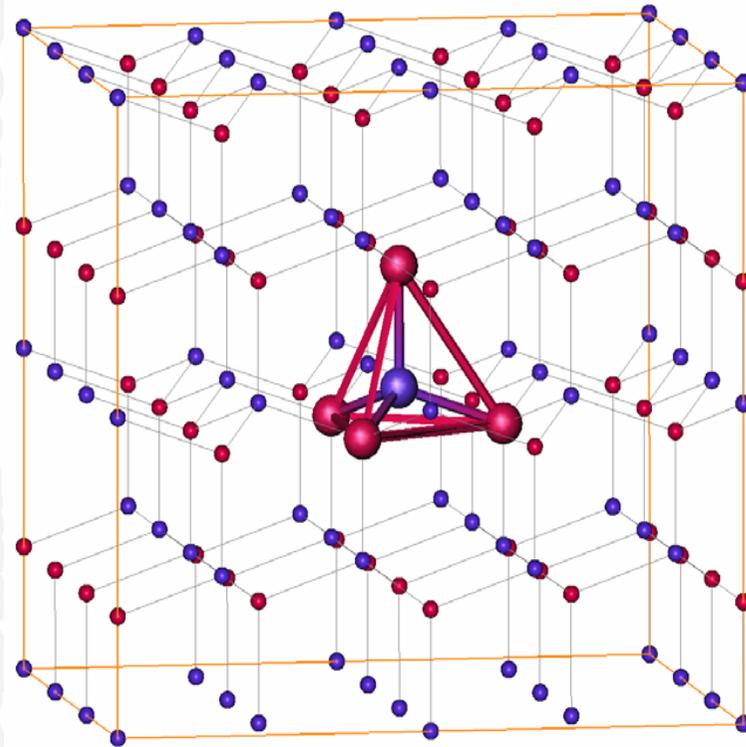
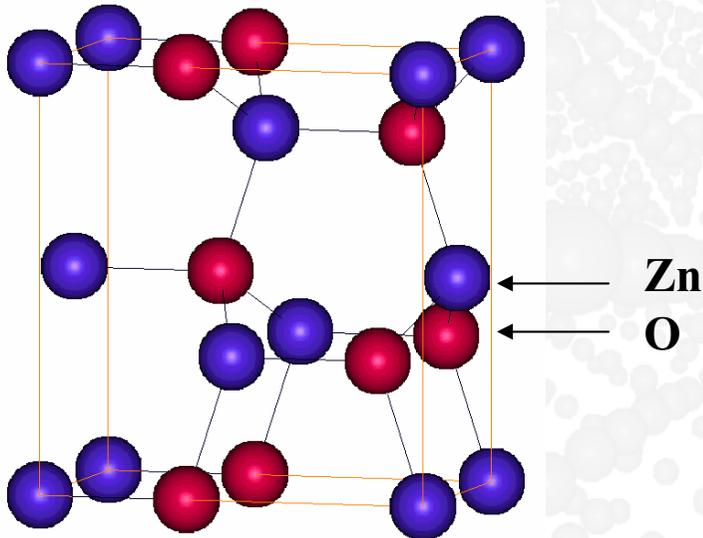
- ZrO₂ (YSZ)

ZnO-motivation

- ✿ ZnO is a wide band gap semiconductor (~ 3.4 eV).
- ✿ Defect identification in ZnO is of great importance because of prospective applications in electronics.
- ✿ Positrons may help to identify open volume defects.
- ✿ ZnO contains large amount of hydrogen and studying H-related defects is necessary.
- ✿ Most of commercial ZnO materials are of n-type and p-type doping is problematic
 - origin: V_O , Zn_i , H-related defects
- ✿ We concentrate on nominally undoped materials and grown in defects.

ZnO-structure

- ✿ ZnO exhibits hexagonal wurtzite structure
 - it is useful to view the structure in terms of ZnO_4 tetrahedra interconnected at corners



ZnO-chemical analysis

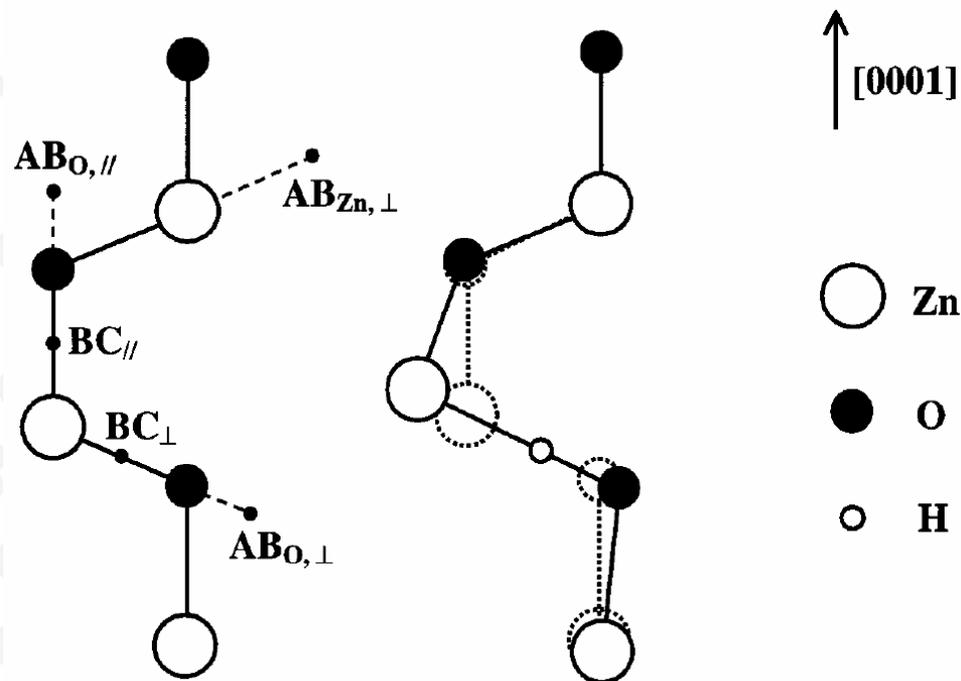
- Nuclear reaction analysis (NRA) measurement of H content in ZnO single crystals revealed the presence of at least 0.3 at.% of H.
- Concentrations of other impurities (obtained via ICP-MS) are small.

G. Brauer et al., PRB **79** (2009) 115212

ZnO + H

H in ZnO lattice

- Interstitial H may act as a donor
 - Van de Walle, PRL 85 (2000) 1012
- Bond center and antibonding positions



Zn-methods

- Obtaining defect configurations in ZnO:
 - VASP (=Vienna ab initio simulation package)
 - projected augmented wave (PAW) pseudopotentials
 - valence electrons: Zn – $4s^2, 3d^{10}$; O – $2s^2, 2p^4$
 - local density approximation
 - 96 atom based supercells used
 - 2 x 2 x 2 k-points in the whole BZ
(symmetry switched off)
 - vacancies created by removing corresponding atoms
 - H atoms added to positions predicted by Van de Walle
 - the total energy of studied defect configurations relaxed with respect to atomic positions (all atoms allowed to move)

ZnO-methods

✿ Positron induced forces:

- treated within the scheme developed by Makkonen et al., PRB 73 (2006) 035103
- conventional scheme for positron calculations considered
- Hellman-Feynman theorem used to calculate forces

$$\mathbf{F}_j = - \langle \psi_+ | \nabla_j V_+(\mathbf{r}, \{\mathbf{R}_i\}) | \psi_+ \rangle$$

- V_+ is constructed using atomic (Coulomb) potentials and densities and force calculation is thus very fast
- such forces added to ionic forces calculated by VASP and atomic positions where total forces vanish are found
- though the method is not fully self-consistent and does not use TCDFT, it is sufficient to get reliable results

ZnO-results

- Bulk lifetime:

- Calculated:

- 154 ps (SC) 153 ps (SC, LMTO) 159 ps (NS)

- Experimental:

- 151, 155-158, 161, 166, 169-173, 176-183 ps

- Plausible assumption: the bulk lifetime is 150-160 ps

ZnO-results

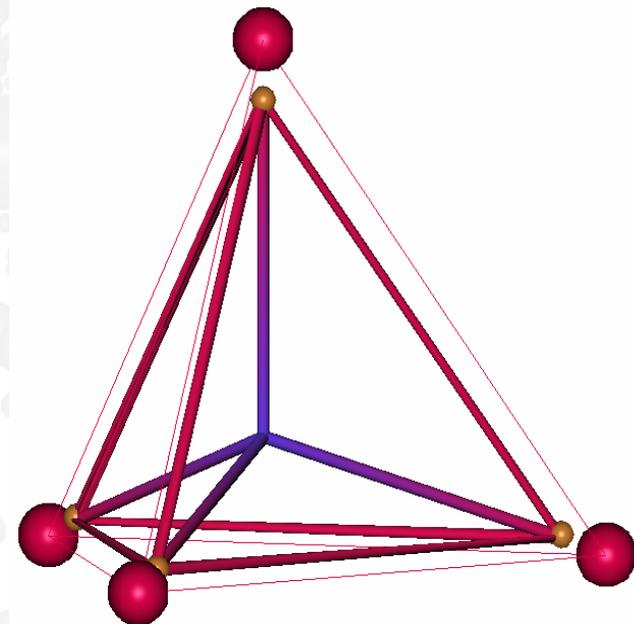
- Oxygen vacancy:

- There is no positron trapping
- Removing oxygen atom is not enough to create sufficiently deep potential well to trap positrons.

ZnO-results

• Zinc vacancy:

- NR NS 194 ps 0.35 eV
 - RE NS 231 ps 0.60 eV
 - RE SC 246 ps 1.25 eV
 - RE SC PF 207 ps 1.11 eV
- Calculated lifetime can be compared with a lifetime of 207 ps observed in electron irradiated ZnO.



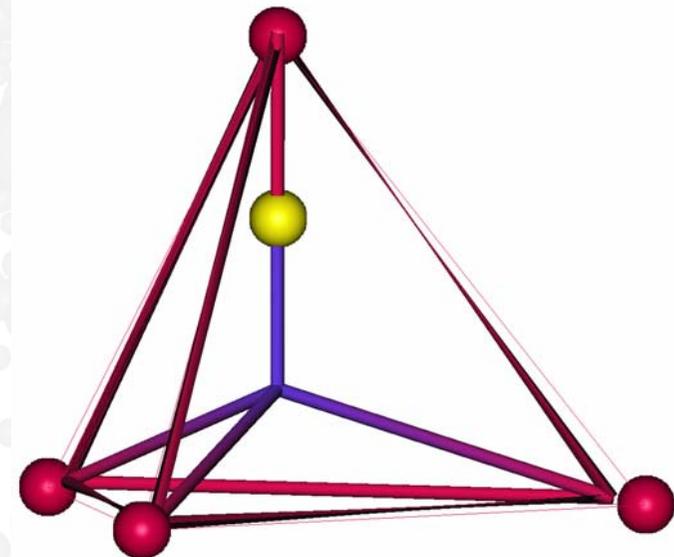
ZnO-results

• $V_{Zn} + 1H$:

■ NR NS	179 ps	0.12 eV
■ RE NS	190 ps	0.19 eV
■ RE SC	199 ps	0.48 eV
■ RE SC PF	177 ps	0.25 eV

- Calculated lifetime can be compared with 169-183 ps measured in various ZnO materials indicating presence of $V_{Zn} - H$ complexes.

- Second configuration:
RE SC PF 179 ps 0.30 eV



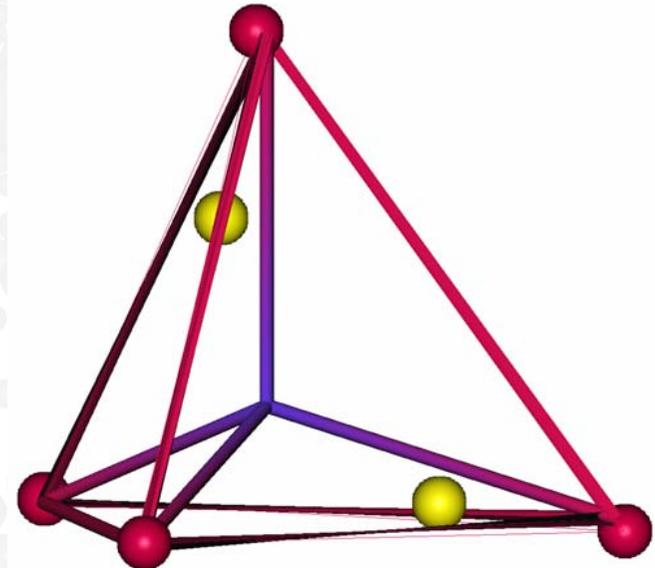
ZnO-results

• $V_{Zn} + 2H$:

■ NR NS	161 ps	~ 0 eV
■ RE NS	163 ps	0.01 eV
■ RE SC	164 ps	0.03 eV
■ RE SC PF	156 ps	~ 0 eV

- This case demonstrates that already 2 H atoms probably fill up zinc vacancy and no trapping is possible.

- Second configuration:
RE SC PF 156 ps ~ 0 eV



ZnO-results

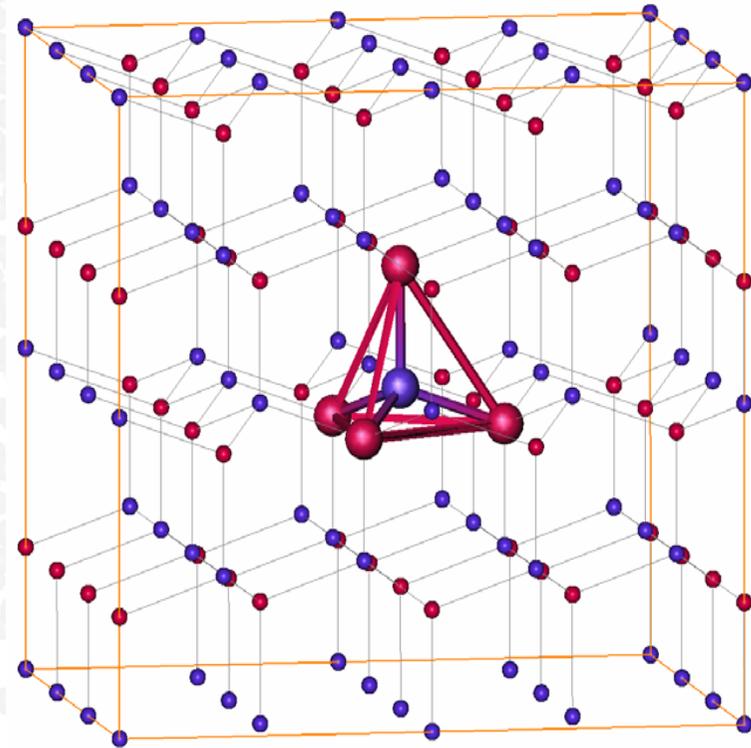
✿ Further observations:

- The H_2 molecule is neither stable in V_{Zn} nor in V_{Zn+O} .
- H-related defects that involve antibonding sites are not stable or have much larger energies than those corresponding to BC sites.
- H binding energies to V_{Zn}
 - ~ 3 eV for 1H
 - ~ 6 eV for 2H
 - ~ 7 eV for 3H
 - ~ 7 eV for 4Hwith respect to H_i positions.

ZnO-results

• Configurations examined:

- V_{Zn+O}
- $V_{Zn+O}+1H$ OV
- $V_{Zn+O}+1H$ Oab
- $V_{Zn+O}+1H$ Oc
- $V_{Zn+O}+2H$ OabV
- $V_{Zn+O}+2H$ OcV
- $V_{Zn+O}+2H$ Oab
- $V_{Zn+O}+2H$ Oabc



ZnO-results

• Positron lifetimes and binding energies:

■ ZnO bulk	154 ps	
■ V_{Zn+O}	225 ps	1.0 eV
■ $V_{Zn+O}+1H$ OV	220 ps	0.9 eV
■ $V_{Zn+O}+1H$ Oab	211 ps	0.8 eV
■ $V_{Zn+O}+1H$ Oc	208 ps	0.7 eV
■ $V_{Zn+O}+2H$ OabV	185 ps	0.4 eV
■ $V_{Zn+O}+2H$ OcV	184 ps	0.4 eV
■ $V_{Zn+O}+2H$ Oab	156 ps	~ 0 eV
■ $V_{Zn+O}+2H$ Oabc	156 ps	~ 0 eV

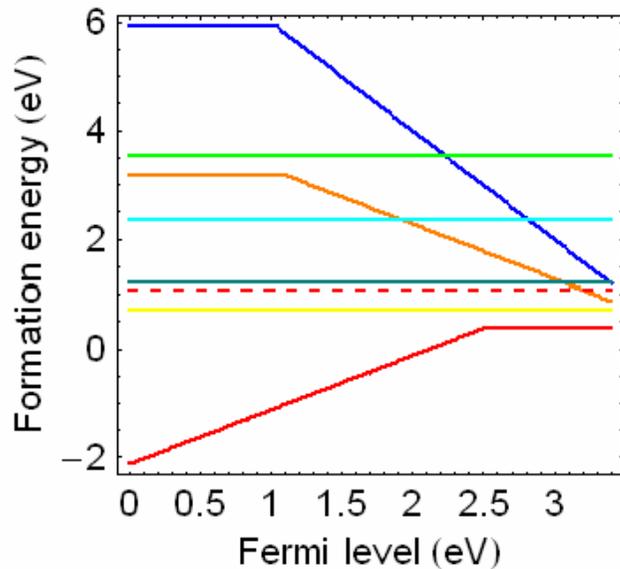
ZnO-results

• Energies of configurations (low, high):

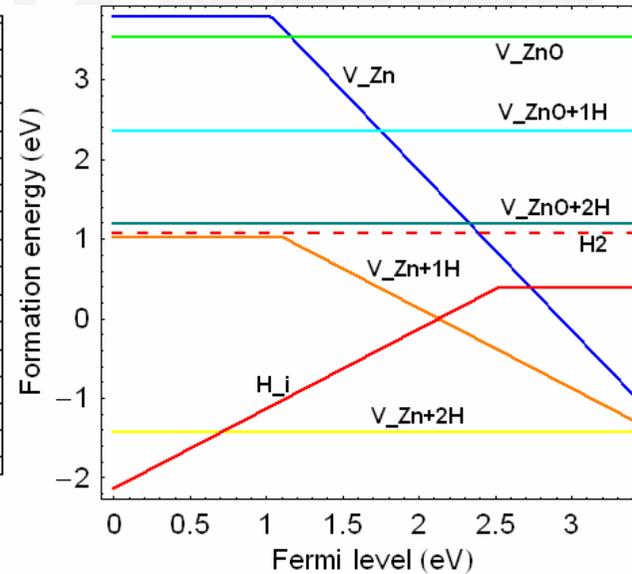
■ $V_{Zn+O}+1H$ OV	220 ps	(1.7eV)
■ $V_{Zn+O}+1H$ Oab	211 ps	
■ $V_{Zn+O}+1H$ Oc	208 ps	
■ $V_{Zn+O}+2H$ OabV	185 ps	(0.2eV)
■ $V_{Zn+O}+2H$ OcV	184 ps	(0.2eV)
■ $V_{Zn+O}+2H$ Oab	156 ps	
■ $V_{Zn+O}+2H$ Oabc	156 ps	

ZnO-results

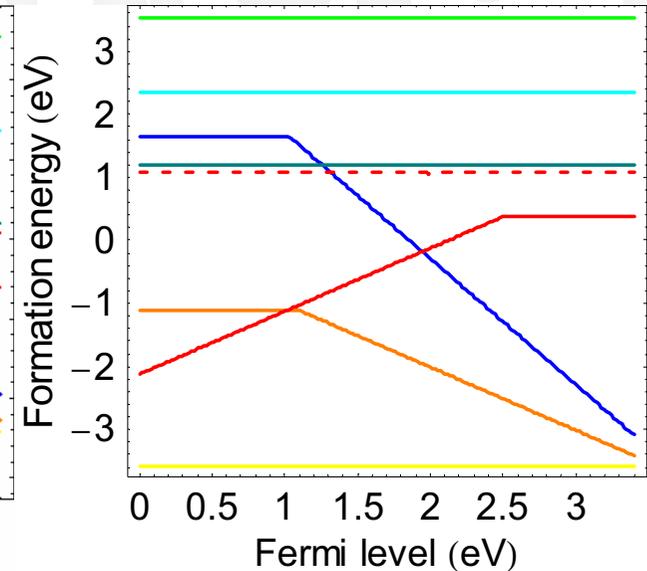
- Defect formation energies:



Zn rich
conditions



intermediate



Zn poor
conditions

ZnO-conclusions

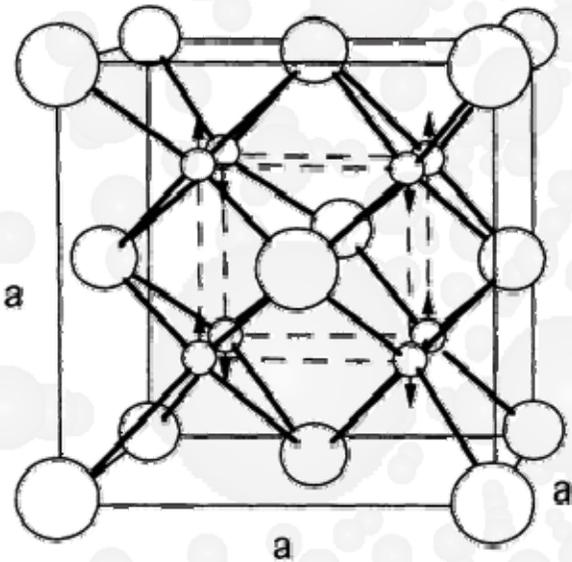
- Both the charge transfer between cations and anions as well as relaxations of defect configurations including positron induced forces are important to get reliable results.
- Oxygen vacancy does not trap positrons.
- One hydrogen atom reduces significantly the positron lifetime of the zinc vacancy.
- Two hydrogen atoms fill up V_{Zn} so that positron trapping is not possible.

ZnO-conclusions

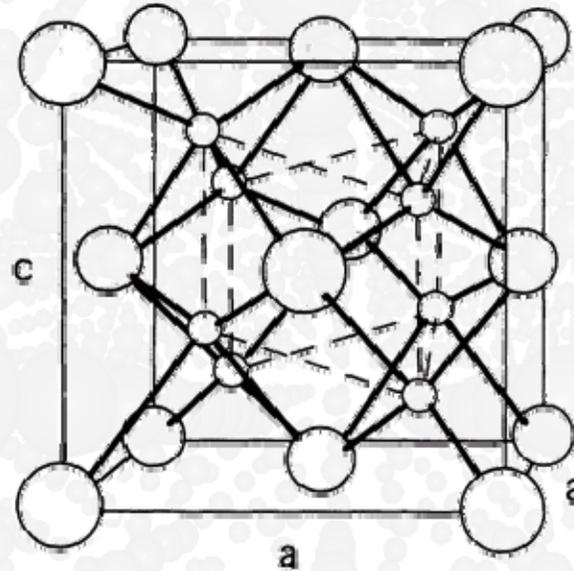
- V_{Zn+O} is a deep positron trap and its positron lifetime is very close to lifetimes observed in some experiments.
- When one H atom is bound inside V_{Zn+O} the positron lifetime is reduced significantly and is close to that for V_{Zn} .
- Some of $V_{Zn+O}+2H$ complexes trap positrons, but their energy is relatively high so that they may not contribute to positron annihilation response from ZnO samples.
- Defects in various charge states need to be studied.

ZrO₂-structure

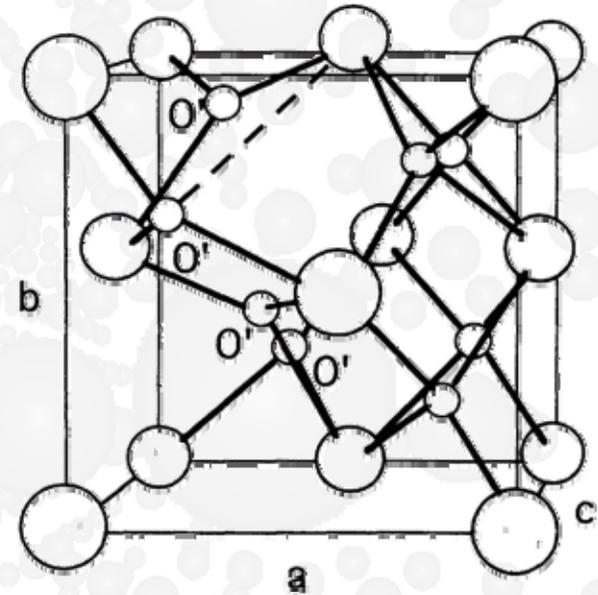
- Three structures of ZrO₂ at ambient pressure:



cubic structure (CaF₂)
above ~1380 °C



tetragonal structure
above ~1200 °C



monoclinic structure

ZrO₂-introduction

- ZrO₂ (zirconia):
 - high melting point (2700 °C)
 - low thermal conductivity
 - good oxygen-ion conductivity (higher temperatures)
 - high strength
 - enhanced fracture toughness
- For applications stabilization of the tetragonal or cubic phase is necessary.
- Zirconia is often stabilized by yttria (Y₂O₃) → yttria stabilized zirconia (YSZ)

ZrO₂-introduction

- Zr has +4 charge state (Zr^{IV}) and Y is +3 only (Y^{III}), i.e. -1 with respect to the lattice
- ⇒ compensation by O vacancies having +2 charge state (V_O^{••})
- there are two Y^{III} per one V_O^{••}
- stability ranges:
 - > 8 mol% of Y₂O₃ → cubic phase
 - > 3 mol% of Y₂O₃ → tetragonal phase
- ⇒ large amount of vacancies in YSZ materials

ZrO₂-recent results

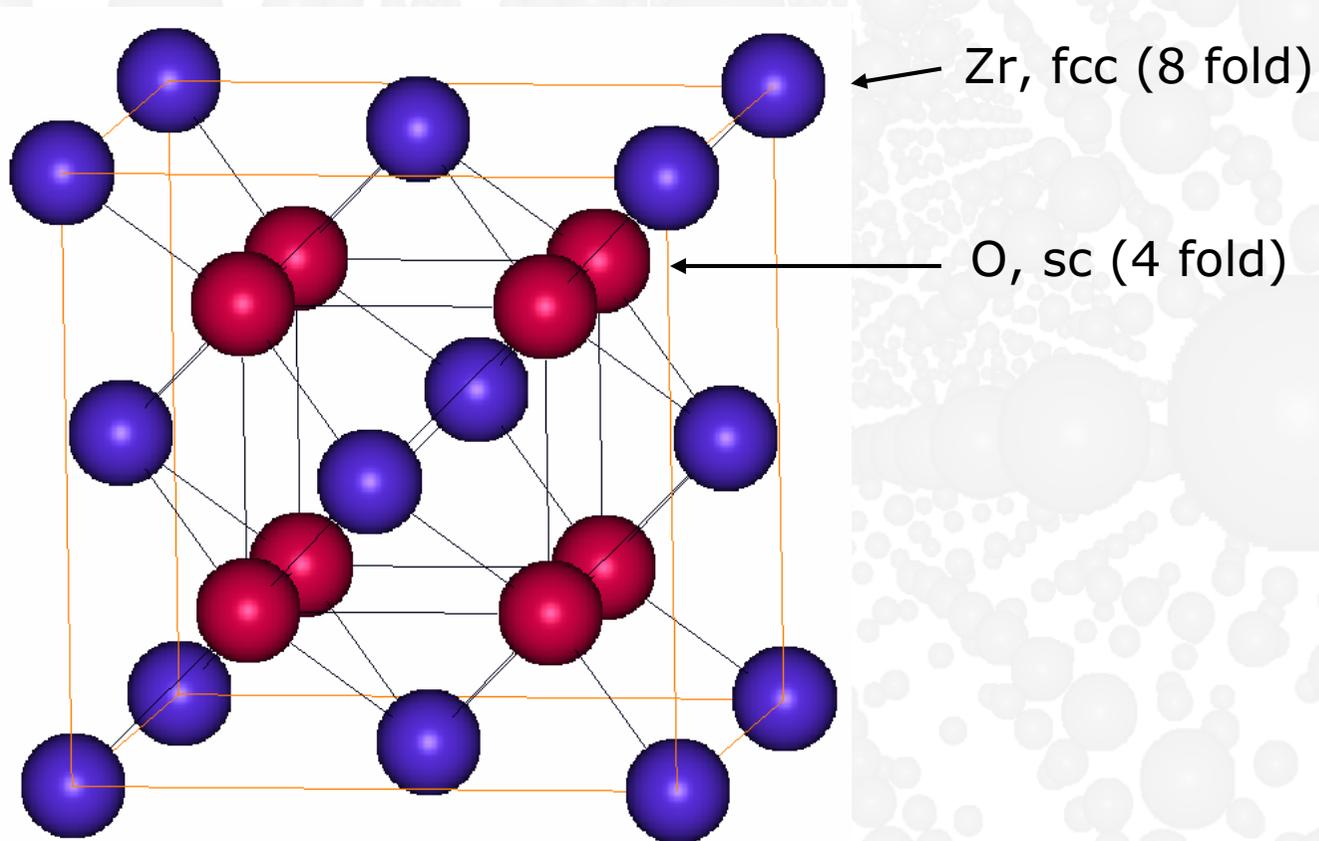
- Cubic YSZ single crystal (8 mol% of Y₂O₃) → 175 ps positron lifetime.
- Before we studied the following vacancy-like defects:
 - V_{Zr}, V_O, V_O-2Y, 2V_O-4Y (V_O's along [111] direction)
 - positron trapping at V_{Zr} only (but too long lifetime)

ZrO₂-motivation

- H is everywhere ...
- First NRA results indicate that we have appreciable amount of H in our sample.
- What are the positions of H in ZrO₂ lattice.

ZrO₂-structure

- ZrO₂ (CaF₂) structure:



ZrO₂-methods

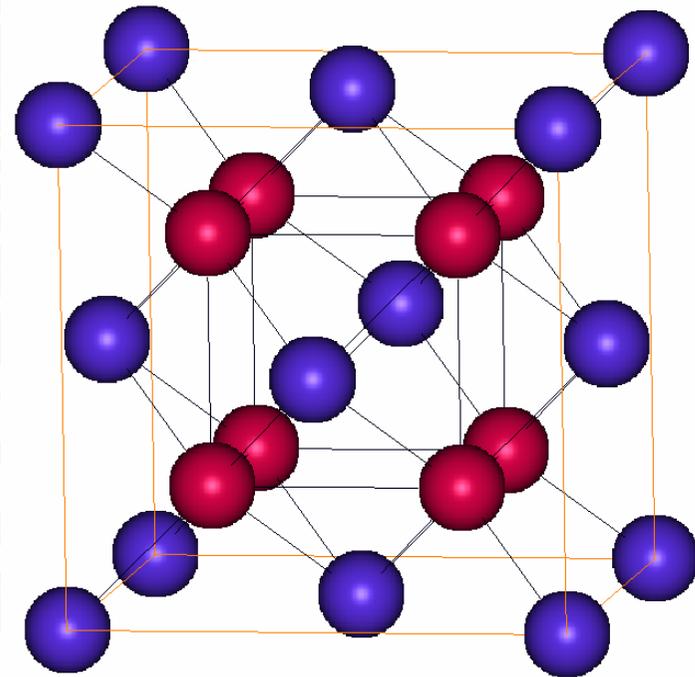
- ❁ Defect configurations:
 - obtained using VASP-PAW, LDA & GGA
 - 96 atom based supercells
 - total energy of studied defect configurations relaxed with respect to atomic positions
 - cubic structure unstable (without Y) !!

ZrO₂-methods

- Configurations examined:

- Interstitial hydrogen

- Hydrogen in V_{Zr}



ZrO₂-results

• Cubic phase:

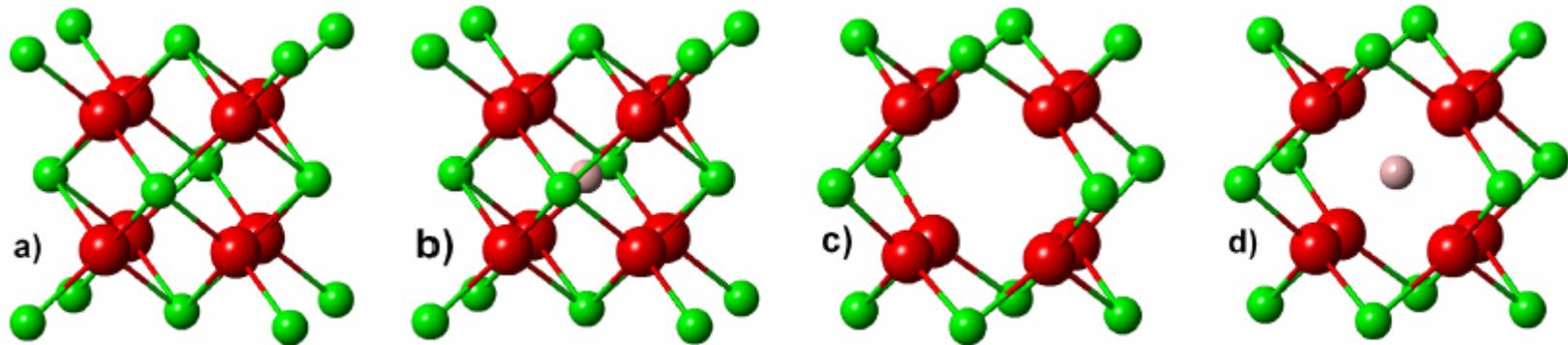


Figure 1. Cubic ZrO₂: a) perfect lattice, b) H in the O₈ interstitial space, c) V_{Zr}, and d) H in the center of V_{Zr}. Red, green, and pink spheres represent, respectively, O, Zr, and H atoms.

ZrO₂-results

• Tetragonal phase:

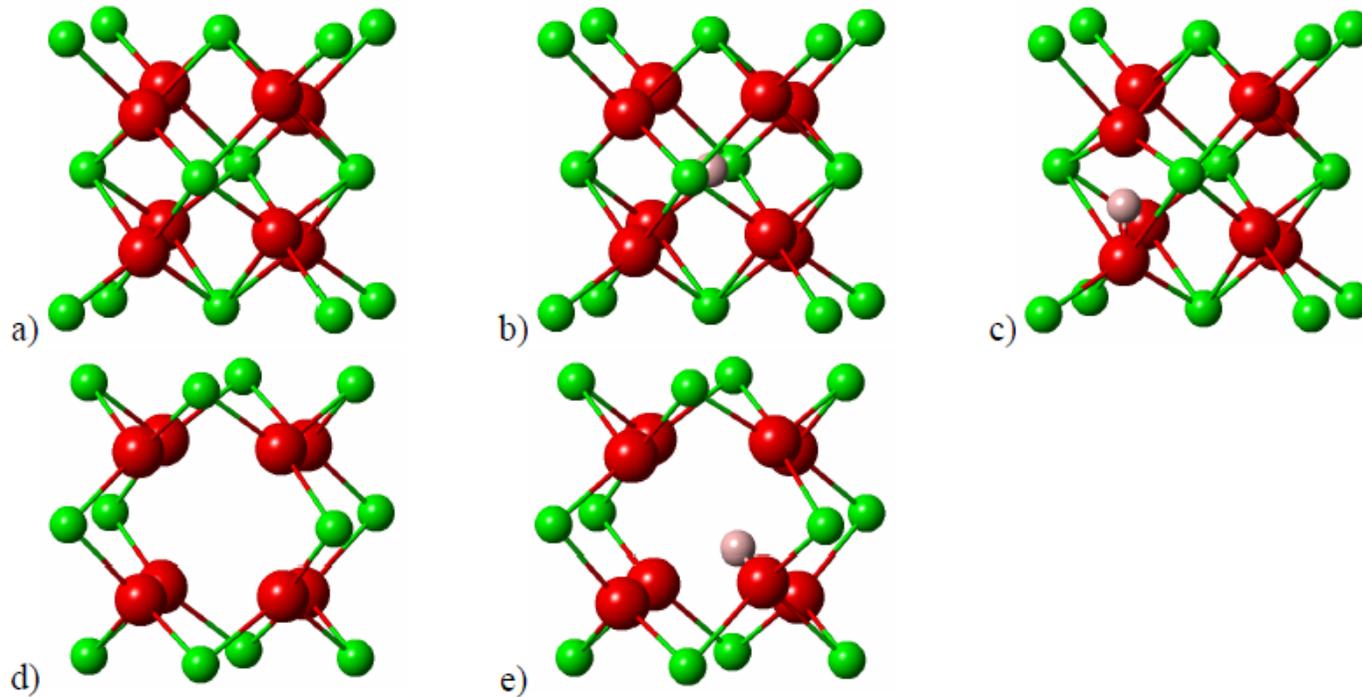


Figure 2. Tetragonal ZrO₂: a) perfect lattice, b) H in the center of the interstitial space, c) H bound to an oxygen atom, d) V_{Zr}, and e) H in V_{Zr}. Sphere designation is the same as in figure 1.

ZrO₂-results

- Positron lifetimes and binding energies (LDA/GGA):

Table I. Positron characteristics of studied open volume defects.

Configuration	BN		GC		BN		GC	
	τ (ps)	E_b (eV)	τ (ps)	E_b (eV)	τ (ps)	E_b (eV)	τ (ps)	E_b (eV)
Cubic phase								
Bulk	138	–	146	–	133	–	157	–
V_{Zr}	216	2.75	238	2.60	220	2.81	291	2.42
$V_{Zr}+1H$ (center)	169	1.76	181	1.68	167	1.28	199	1.31
Tetragonal phase								
Bulk	138	–	146	–	133	–	158	–
V_{Zr}	216	2.74	238	2.59	219	2.76	291	2.37
$V_{Zr}+1H$	189	2.23	204	2.12	189	1.76	237	1.54
	ATSUP				ATSUP+VASP			

H in V_{Zr} can in principle explain lifetime data !!

ZrO₂-conclusions

- We have studied H positions in the zirconia lattice.
- In the case of the interstitial H the lowest energy configuration is for H bound to an O atom near the center of the interstitial space (tetragonal, O-H bond formed).
- As for the V_{Zr} , H prefers position close to a neighboring O atom (tetragonal, O-H bond formed).
- The latter defect traps positrons and could be responsible for the observed positron lifetime.

ZrO₂-outlook

- More H-related configurations needed.
- The question of the cubic YSZ structure needs to be solved.



T h a n k y o u !